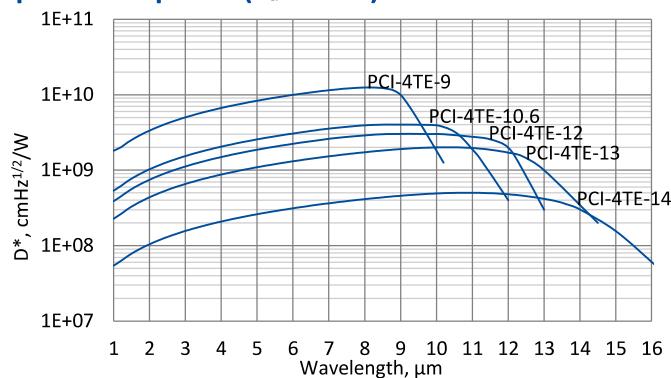


## PCI-4TE series

### 1 – 16 $\mu\text{m}$ HgCdTe four-stage thermoelectrically cooled, optically immersed photoconductive detectors

**PCI-4TE series** features four-stage thermoelectrically cooled IR photoconductive detectors based on sophisticated HgCdTe heterostructures for the best performance and stability, optically immersed in order to improve parameters of the devices. The detectors are optimized for the maximum performance at  $\lambda_{\text{opt}}$ . Cut-on wavelength is limited by GaAs transmittance ( $\sim 0.9 \mu\text{m}$ ). The devices should operate in optimum bias voltage and current readout mode. Performance at low frequencies is reduced due to 1/f noise. The 1/f noise corner frequency increases with the cut-off wavelength. 3° wedged zinc selenide anti-reflection coated (wZnSeAR) window prevents unwanted interference effects.

#### Spectral response ( $T_a = 20^\circ\text{C}$ )



Exemplary spectral detectivity, the spectral response of delivered devices may differ.

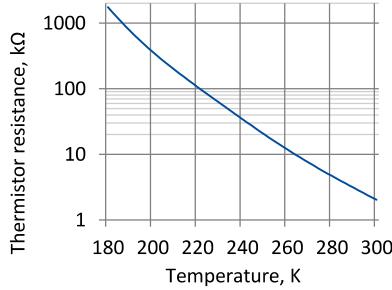
#### Specification ( $T_a = 20^\circ\text{C}$ )

Parameter	Detector type				
	PCI-4TE-9	PCI-4TE-10.6	PCI-4TE-12	PCI-4TE-13	PCI-4TE-14
Active element material	epitaxial HgCdTe heterostructure				
Optimal wavelength $\lambda_{\text{opt}}$ , $\mu\text{m}$	9.0	10.6	12.0	13.0	14.0
Detectivity $D^*(\lambda_{\text{peak}}, 20\text{kHz})$ , $\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$	$\geq 1.25 \times 10^{10}$	$\geq 4.0 \times 10^9$	$\geq 3.0 \times 10^9$	$\geq 2.0 \times 10^9$	$\geq 5.0 \times 10^8$
Detectivity $D^*(\lambda_{\text{opt}}, 20\text{kHz})$ , $\text{cm} \cdot \text{Hz}^{1/2}/\text{W}$	$\geq 1.0 \times 10^{10}$	$\geq 3.0 \times 10^9$	$\geq 2.0 \times 10^9$	$\geq 1.0 \times 10^9$	$\geq 3.0 \times 10^8$
Current responsivity-optical area length product $R_i(\lambda_{\text{opt}}) \cdot L_o$ , $\text{A} \cdot \text{mm}/\text{W}$	$\geq 0.9$	$\geq 0.2$	$\geq 0.09$	$\geq 0.05$	$\geq 0.03$
Time constant $\tau$ , ns	$\leq 80$	$\leq 30$	$\leq 7$	$\leq 6$	$\leq 5$
1/f noise corner frequency $f_c$ , Hz	$\leq 10k$		$\leq 20k$		
Bias voltage-optical area length ratio $V_b/L_o$ , V/mm	$\leq 0.3$		$\leq 0.24$		$\leq 0.18$
Resistance $R$ , $\Omega$	$\leq 500$		$\leq 400$		$\leq 300$
Active element temperature $T_{\text{det}}$ , K			$\sim 195$		
Optical area $A_o$ , mm $\times$ mm			$0.5 \times 0.5$ , $1 \times 1$ , $2 \times 2$		
Package			TO8, TO66		
Acceptance angle $\Phi$			$\sim 36^\circ$		
Window			wZnSeAR		

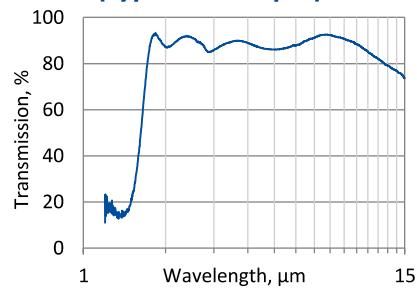
#### Four-stage thermoelectric cooler parameters

Parameter	Value
$T_{\text{det}}$ , K	$\sim 195$
$V_{\text{max}}$ , V	8.3
$I_{\text{max}}$ , A	0.4
$Q_{\text{max}}$ , W	0.28

#### Thermistor characteristics

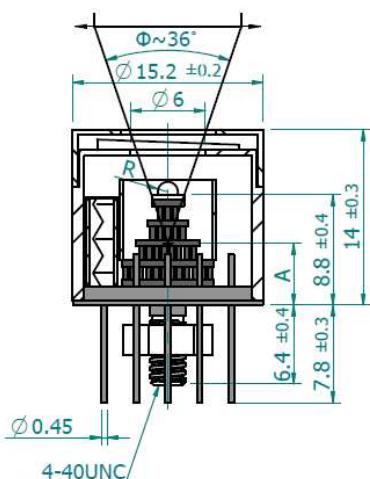


#### Spectral transmission of wZnSeAR window (typical example)



## Mechanical layout, mm

### 4TE-T08 package



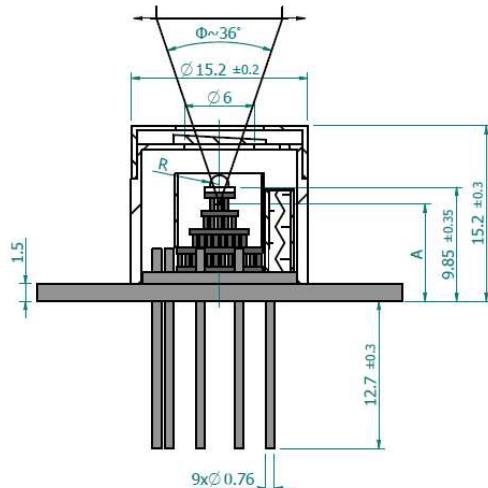
Parameter	Value		
Immersion microlens shape	hyperhemisphere		
Optical area $A_0$ , mm×mm	0.5×0.5	1×1	2×2
R, mm	0.5	0.8	1.25
A, mm	7.3±0.4	6.4±0.4	5.0±0.4

Φ – acceptance angle

R – hyperhemisphere microlens radius

A – distance from the bottom of 4TE-T08 header to the focal plane

### 4TE-T066 package



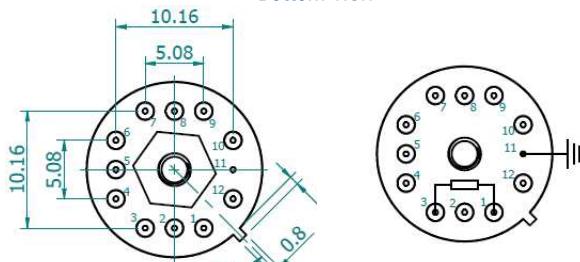
Parameter	Value		
Immersion microlens shape	hyperhemisphere		
Optical area $A_0$ , mm×mm	0.5×0.5	1×1	2×2
R, mm	0.5	0.8	1.25
A, mm	8.35±0.40	7.45±0.40	6.1±0.4

Φ – acceptance angle

R – hyperhemisphere microlens radius

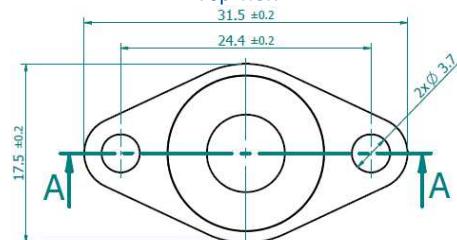
A – distance from the bottom of 4TE-T066 header to the focal plane

#### Bottom view

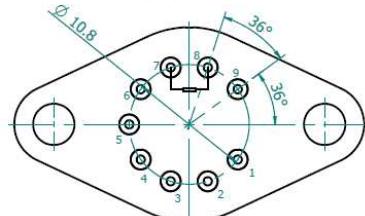


Function	Pin number
Detector	1, 3
Thermistor	7, 9
TE cooler supply	2(+), 8(-)
Chassis ground	11
Not used	4, 5, 6, 10, 12

#### Top view



#### Bottom view



Function	Pin number
Detector	7, 8
Thermistor	5, 6
TE cooler supply	1(+), 9(-)
Not used	2, 3, 4

## Dedicated preamplifiers



„all-in-one“ AIP



programmable PIP



standard MIP



small SIP-T08